

Micro-miniature OCXO



ESD Sensitive

20.3 x 12.7 x 11 mm

Datasheet #0635A

Features

- Low Cost DIL 14 package
- High Vacuum Sealed Crystal
- Low Power Consumption (500 mW)
- Fast Warm-up Time (2 minutes)
- Stratum3 or better Stability
- Low Aging less than 3ppm over life
- Very Low Phase Noise (-155dBc/Hz TYP)
- HCMOS/TTL or Sine-Wave output
- 8 MHz to 160 MHz Frequencies Available
- Voltage Control Option

Applications

- Telecommunications
- Data Communications
- Instrumentation
- COTS/Dual use

Absolute Maximum Ratings

Parameters	Symbol	Condition	Min	Typ	Max	Unit	Notes
Input Break Down Voltage	V _{cc}		-0.5		5.5	V	3.3V or 5V V _{cc}
Storage temper.	T _s		-40		85	°C	
Control Voltage	V _c		-1		6	V	

Electrical (3*)

Parameters	Symbol	Condition	Min	Typ	Max	Unit	Notes	
Frequency	F		8	10.000	160	MHz	1*	
Frequency stability	ΔF/F	vs. Temp.		±100	±280	ppb	See chart below	
		vs. Supply		10	50	ppb/V		
Aging		per day		5E-9			after 30 days	
		first year		3E-7				
		15 years			3E-6			
Allan deviation		.1s to 100s		5E-11			All parameters for 10 MHz	
Calibration		No voltage control		±0.5	±2	ppm		
V _{cc} sensitivity				5E-8/V				
Load sensitivity		For 10% change			5E-8			
SSB Phase Noise		10 Hz		-100		dBc/Hz		2*
		100 Hz		-130				
		1 KHz		-140				
		10 KHz		-150				
		>100 KHz		-155				
Retrace		After 30 minutes			±100	ppb		
G-sensitivity		worst direction			±2.0	ppb/G		
Input Voltage	V _{cc}		4.75 3.15	5.0 3.3	5.25 3.45	V	See chart below	
Power consumption	P	steady state, 25°C steady state, -30°C start-up		0.5	0.7 1.5 2.5	W	Upper operating temperature <70°C, add 20% for UOT 85°C	
Load		10KOhm//15pF Internally AC coupled 50 Ohm					CMOS Output Sine-wave output	

Micro-miniature OCXO



ESD Sensitive

20.3 x 12.7 x 11 mm

Datasheet #0635A

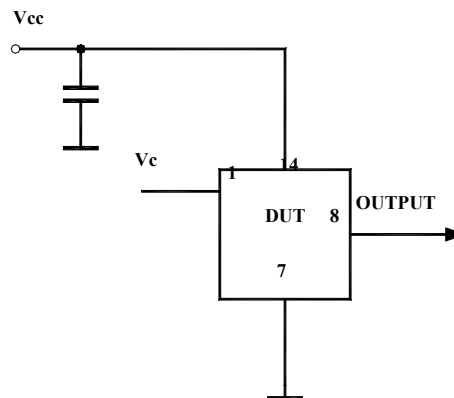
Electrical (cont.)

Parameters	Symbol	Condition	Min	Typ	Max	Unit	Notes
Warm-up time	τ	to 0.3 ppm accuracy		2	3	min	
Sub-Harmonics				-50	-40	dBc	At higher F 1*
Output Waveform		3.3V HCMOS/TTL compatible, 4 ns Tr/Tf, 40/60% duty cycle Sine-wave, +7 dBm \pm 3 dBm into 50 Ohm, -30 dBc harmonics					See chart below
Control Voltage	Vc		0		4.0	V	
Pull range		from nominal F	\pm 5	\pm 10		ppm	Customer specified
Deviation slope		Monotonic, posit		5		ppm/V	Customer specified
Setability	Vc0	@25°C, Fnom	1.0	2.0	3.0	V	5V/3.3 supply
Modulation Bandwidth	Fm		DC		1	KHz	4*

Environmental and Mechanical

Parameter	Description
Operating temp. range	-30°C to 70°C Standard, Other options - see chart below
Mechanical Shock	Per MIL-STD-202, 30G, 11ms
Vibration	Per MIL-STD-202, 5G to 2000 Hz
Soldering Conditions	Leads Temperature 260°C, for 10s, Max
Hermetic seal	Leak rate less than 1×10^{-8} atm. ccm/s of helium

Test Circuit





Creating a Part Number

OC - X 87 X X XX X - X - XXX.XXX MHZ - X

Package Code
OC → 0.8x0.5" 4 pin (14 pin)

Supply Voltage	
Code	Specification
0	5V ± 5%
A	3.3V ± 5%

Voltage Control	
Code	Specification
V	Voltage Control
0	No Voltage Control

Output	
Code	Specification
T	TTL / CMOS
S	Sine

Temperature Stability	
Code	Specification
58	5x10 ⁻⁸
17	1x10 ⁻⁷
S3	2.8x10 ⁻⁷
37	3x10 ⁻⁷
57	5x10 ⁻⁷
YZ	Yx10 ^{-Z}

Packaging	
Blank	Bulk

Output Frequency
Please specify the frequency in units of MHz out to 3-digit accuracy after the decimal.
Example: 10.000MHZ

Environmental	
Code	Specification
L	Contains a level of lead that is in excess of RoHS directive and is not designed for reflow
R	RoHS compliant, not designed for reflow

Temperature Range	
Code	Specification
A	0°C to 50°C
B	0°C to 70°C
C	-20°C to 70°C
D	-40°C to 85°C
E	-10°C to 60°C
F	-40°C to 80°C
G	-30°C to 70°C
9	Customer Specific

Not all combinations are available. Consult Factory.

Temperature Code Table

Letter	Temp °C	Letter	Temp °C	Letter	Temp °C	Letter	Temp °C	Letter	Temp °C	Letter	Temp °C
A	-40	F	-15	K	10	P	35	U	60	Z	85
B	-35	G	-10	L	15	Q	40	V	65		
C	-30	H	-5	M	20	R	45	W	70		
D	-25	I	0	N	25	S	50	X	75		
E	-20	J	5	O	30	T	55	Y	80		

Micro-miniature OCXO



ESD Sensitive

20.3 x 12.7 x 11 mm

Datasheet #0635A

Notes:

1* Higher frequencies can be achieved either by using higher frequency crystals or by low noise analog harmonic multiplication. Both methods have advantages and drawbacks. If lowest possible phase noise on the noise floor is most important-high frequency crystal will be used. If phase noise close to the carrier and aging are more important- multiplication will be used. Please consult the factory for your specific requirement.

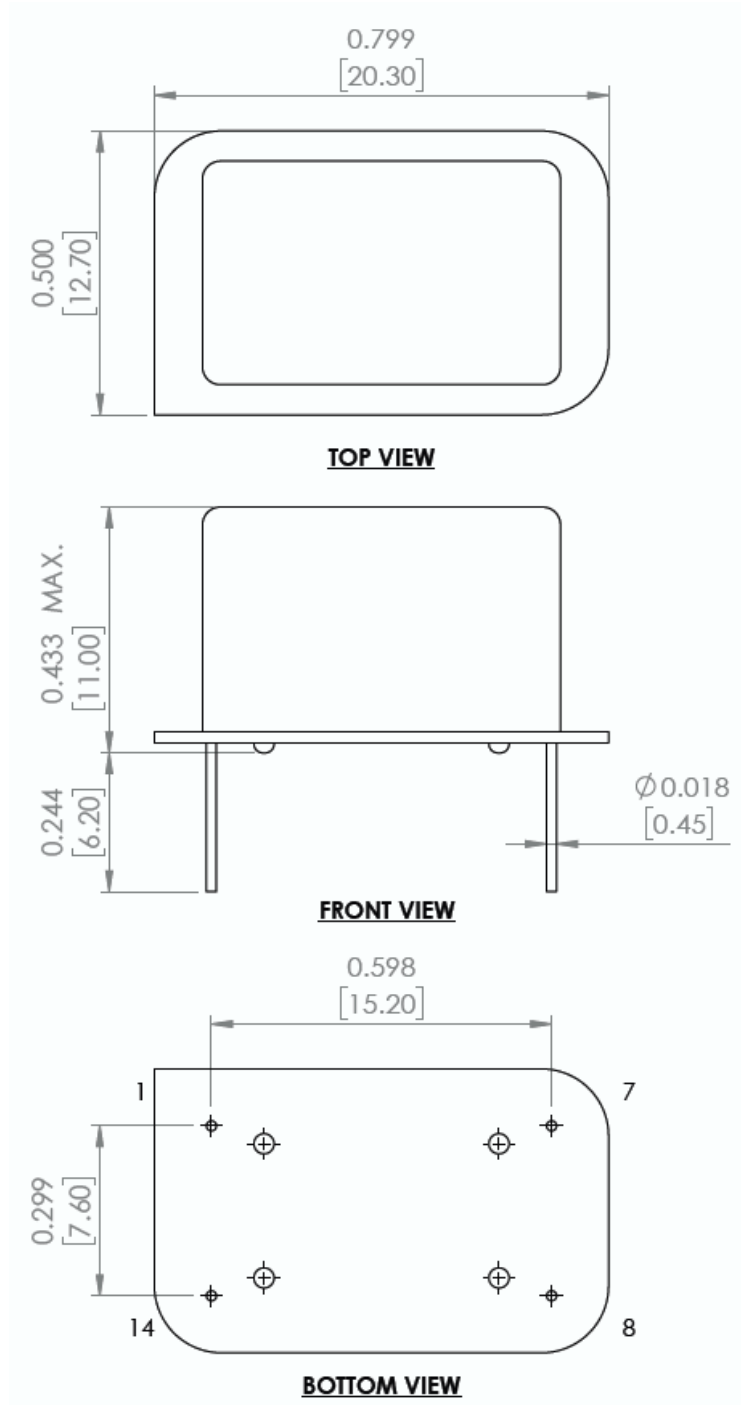
2* Phase noise deteriorates with frequencies going higher. If analog multiplication is used to achieve higher frequency the phase noise roughly follows the formula of additional $20\text{Log}N$, where N is a multiplication factor across entire frequency offset range. If higher frequency is achieved by using higher frequency crystal phase noise close to the carrier deteriorates due to the lower Q of the crystal and is usually worse, compared to multiplied solution. On the noise floor, however it remains more or less the same.

3* All parameters, unless otherwise specified, are at nominal conditions, ie: T=25°C, Nominal Vcc & Nominal Load.

4* Older and stock units may have MBW of 150 Hz Max



Mechanical Dimensions



Pin #	Function
1	Vc
7	Case, GND
8	Output
14	Vcc

Dimensions: inches [mm]